

این دیتاشیت توسط توکل الکترونیک تهیه و ارائه شده است.

جهت مشاهده قیمت، موجودی و ثبت سفارش این قطعه به وبسایت توکل الکترونیک مراجعه فرمایید.



مشاهده قیمت و خرید
برای خرید و مشاهده سایر محصولات کلیک کنید



Ordering number : EN5315A

N-Channel Silicon MOSFET

2SK2349

SANYO

High-Voltage, High-Speed
Switching Applications

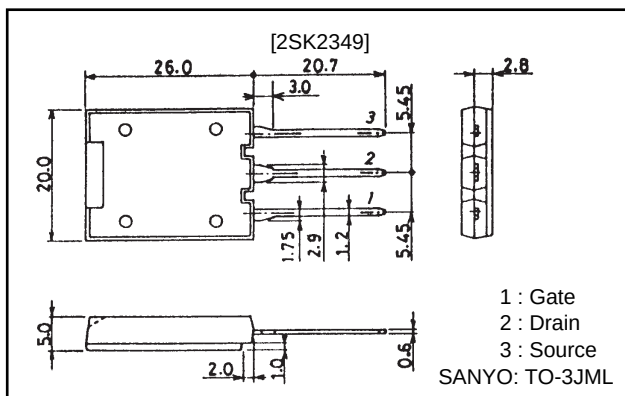
Features

- Low ON resistance, ultrahigh-speed switching.
- High reliability (Adoption of HVP process).

Package Dimensions

unit: mm

2131-TO-3JML



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		1500	V
Gate-to-Source Voltage	V _{GSS}		±30	V
Drain Current (DC)	I _D		10	A
Drain Current (pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	20	A
Allowable Power Dissipation	P _D		4.6	W
		T _c =25°C	160	W
Channel Temperature	T _{ch}		150	°C
Storage temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

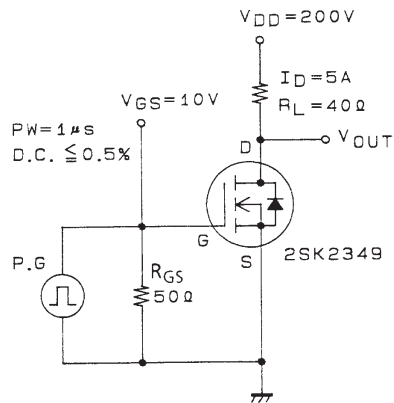
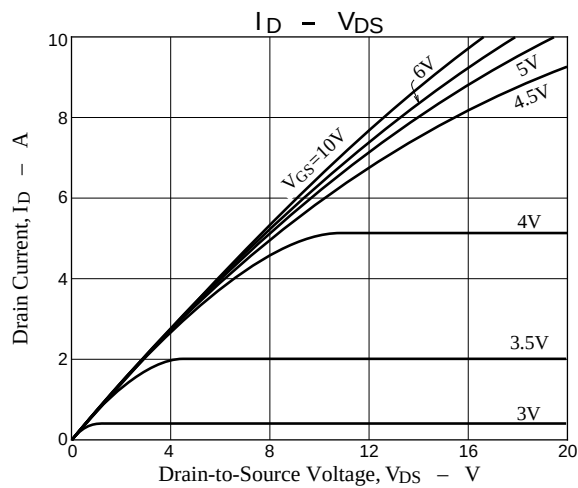
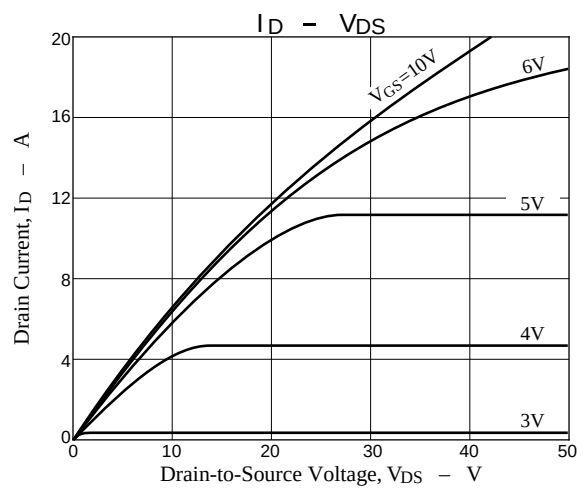
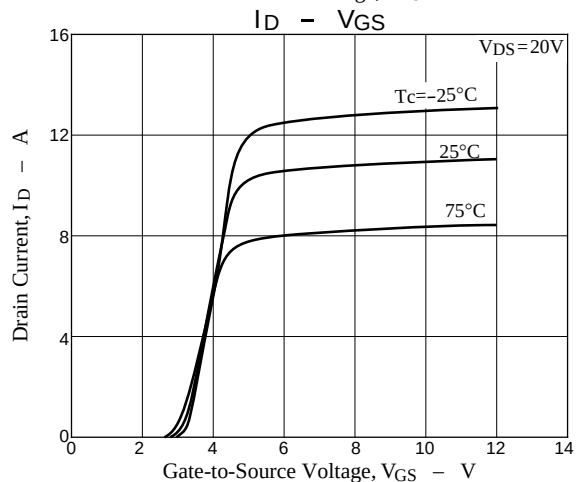
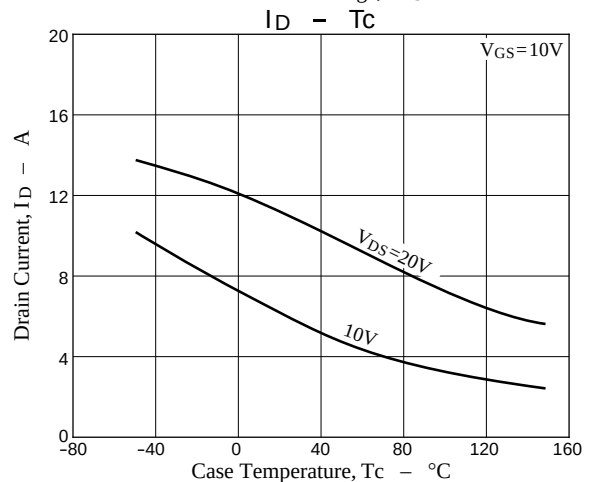
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
D-S Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0	1500			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =1500V, V _{GS} =0			1.0	mA
Gate-to Source Leak Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0			±100	nA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.5		3.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} =20V, I _D =5A	2.0	4.0		S
Static Drain-to-Source ON-State Resistance	R _{DS(on)}	I _D =5A, V _{GS} =10V		1.5	2.5	Ω
Input Capacitance	C _{iss}	V _{DS} =20V, f=1MHz		2900		pF
Output Capacitance	C _{oss}	V _{DS} =20V, f=1MHz		400		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =20V, f=1MHz		200		pF

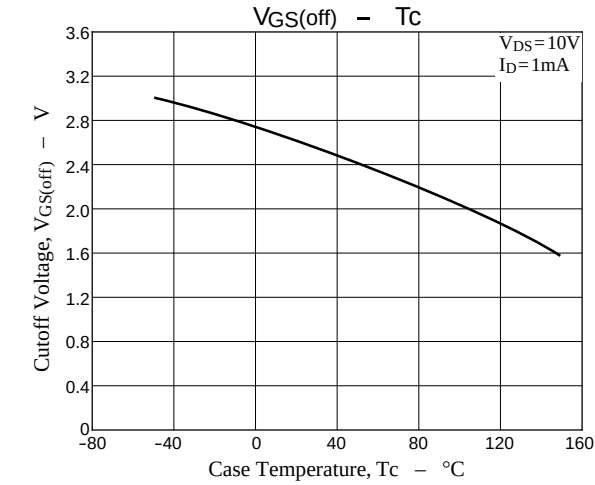
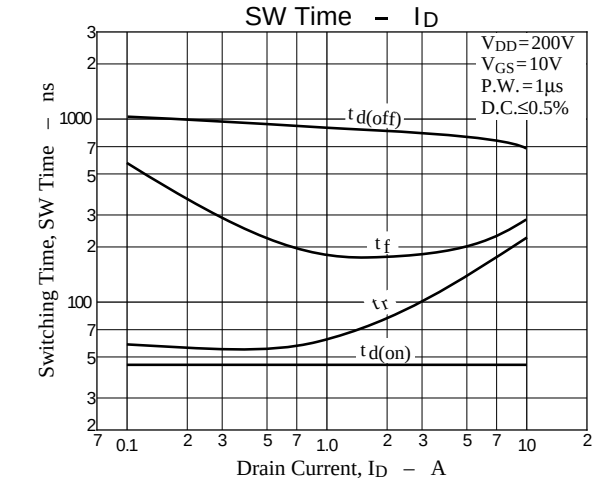
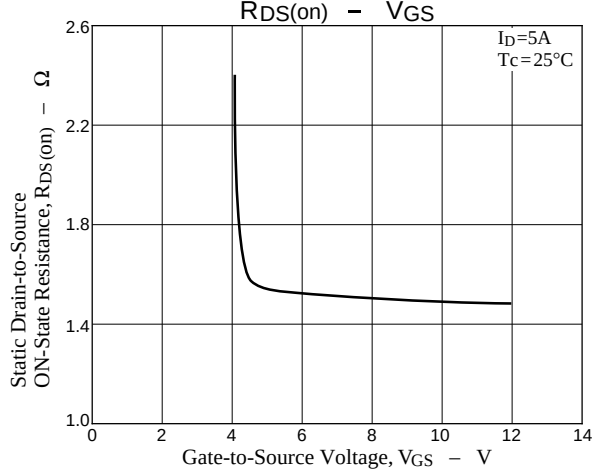
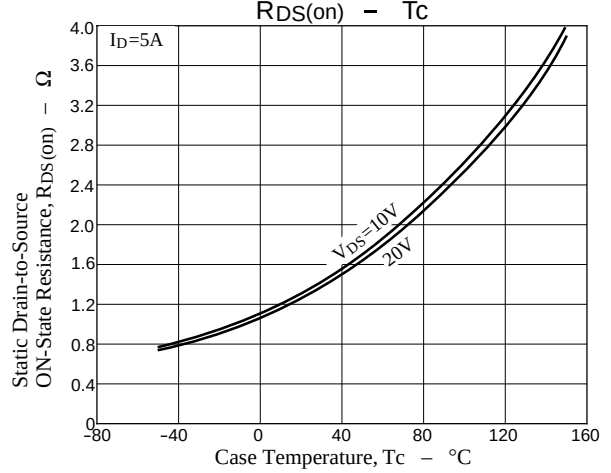
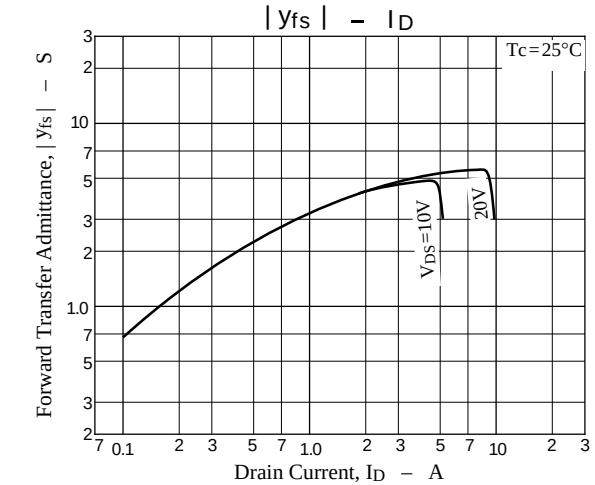
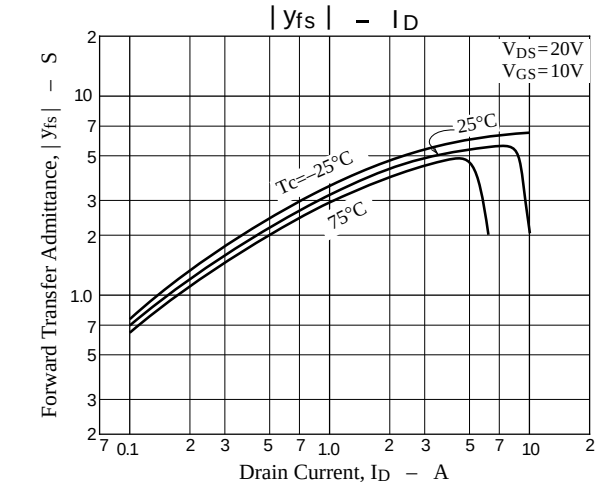
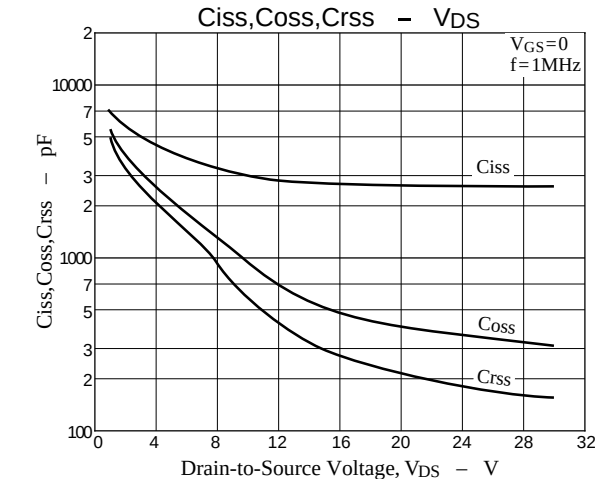
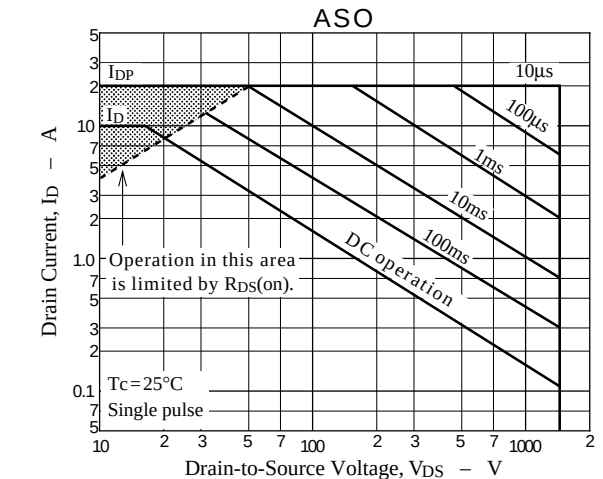
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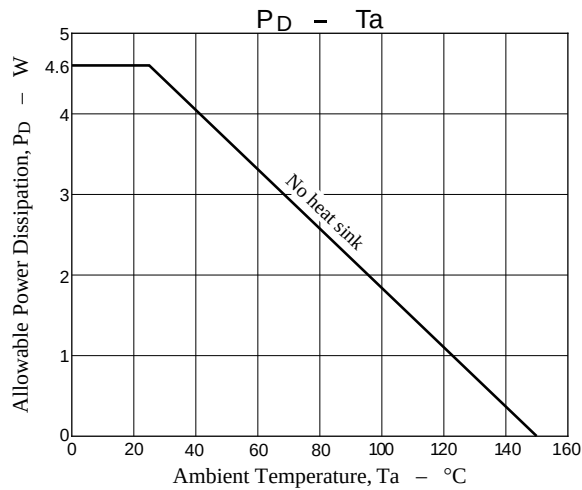
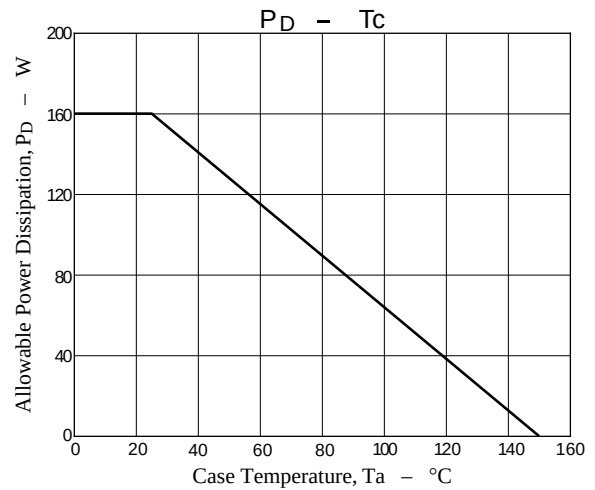
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	$I_D=5A$, $V_{GS}=10V$, $V_{DD}=200V$, $R_{GS}=50\Omega$		45		ns
Rise Time	t_r			150		ns
Turn-OFF Delay Time	$t_{d(off)}$			800		ns
Fall Time	t_f			200		ns
Diode Forward Voltage	V_{SD}	$I_S=10A$, $V_{GS}=0$			1.5	V
Reverse Recovery Time	t_{rr}	$I_S=10A$, $di/dt=100A/\mu s$		1.0	2.0	μs

Switching Time Test Circuit







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